# **Driver Transistors**

### **PNP Silicon**

#### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBTA55 MMBTA56, SMMBTA56	V <sub>CEO</sub>	-60 -80	Vdc
Collector – Base Voltage MMBTA55 MMBTA56, SMMBTA56	V <sub>CBO</sub>	-60 -80	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-4.0	Vdc
Collector Current – Continuous	Ic	-500	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

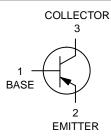


### ON Semiconductor®

#### www.onsemi.com



SOT-23 CASE 318 STYLE 6



### **MARKING DIAGRAM**



2xx = Device Code x = H for MMBTA55LT1G xx = GM for MMBTA56LT1G, SMMBTA56LT1G

M = Date Code\*■ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

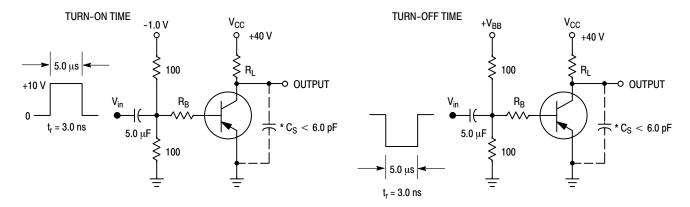
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbo	ol Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0) MMBTA55 MMBTA56, SMMBTA56	V <sub>(BR)CE</sub>	-60 -80		Vdc
Emitter – Base Breakdown Voltage ( $I_E = -100 \mu Adc$ , $I_C = 0$ )	V <sub>(BR)EE</sub>	-4.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = -60 Vdc, I <sub>B</sub> = 0)	I <sub>CES</sub>	-	-0.1	μAdc
Collector Cutoff Current $  (V_{CB} = -60 \text{ Vdc}, I_E = 0) $	Ісво		-0.1 -0.1	μAdc
ON CHARACTERISTICS	<u>.</u>			
DC Current Gain ( $I_C = -10 \text{ mAdc}$ , $V_{CE} = -1.0 \text{ Vdc}$ ) ( $I_C = -100 \text{ mAdc}$ , $V_{CE} = -1.0 \text{ Vdc}$ )	h <sub>FE</sub>	100 100	_ _	_
Collector – Emitter Saturation Voltage ( $I_C = -100 \text{ mAdc}$ , $I_B = -10 \text{ mAdc}$ )	V <sub>CE(sa</sub>	t) _	-0.25	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = -100 mAdc, V <sub>CE</sub> = -1.0 Vdc)	V <sub>BE(or</sub>	) –	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS	·			
Current – Gain – Bandwidth Product (Note 4) $(I_C = -100 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}, f = 100 \text{ MHz})$		50	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>4.</sup> f<sub>T</sub> is defined as the frequency at which |h<sub>fe</sub>| extrapolates to unity.



<sup>\*</sup>Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

<sup>3.</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

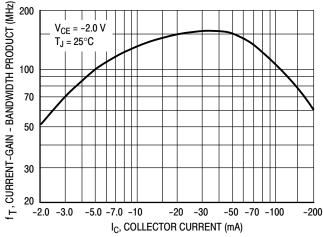


Figure 2. Current-Gain — Bandwidth Product

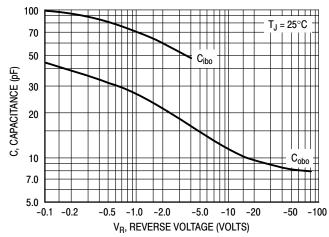


Figure 3. Capacitance

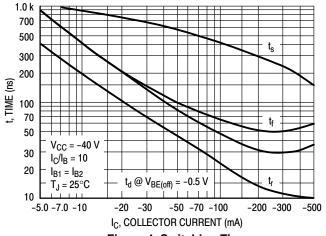


Figure 4. Switching Time

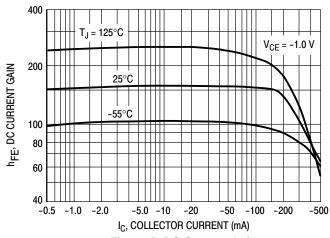


Figure 5. DC Current Gain

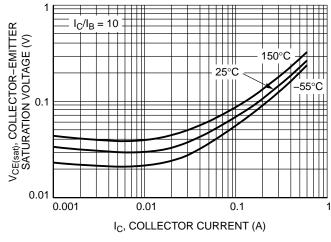


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

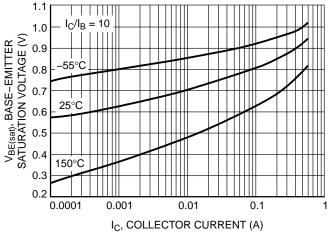


Figure 7. Base Emitter Saturation Voltage vs.
Collector Current

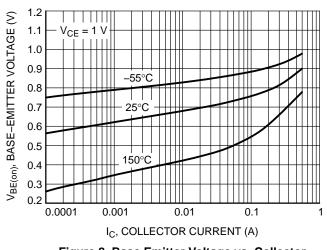


Figure 8. Base Emitter Voltage vs. Collector Current

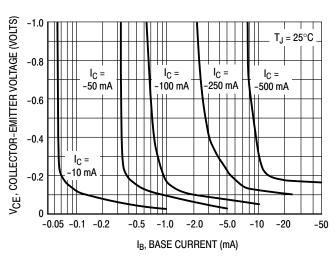


Figure 9. Collector Saturation Region

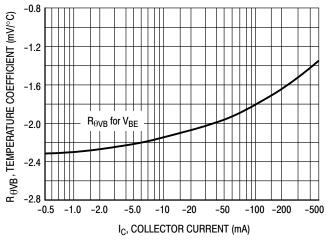


Figure 10. Base–Emitter Temperature Coefficient

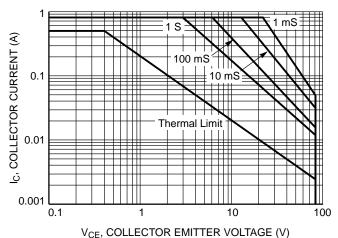


Figure 11. Safe Operating Area

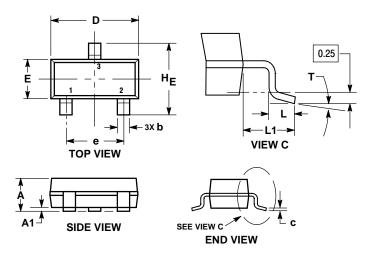
#### **ORDERING INFORMATION**

Device Order Number	Package Type	Shipping <sup>†</sup>
MMBTA55LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA55LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBTA56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBTA56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AS



#### NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

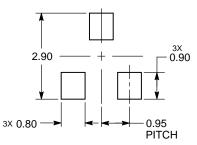
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10 °	0 °	-	10 °

STYLE 6:

PIN 1. BASE **EMITTER** 

COLLECTOR

### RECOMMENDED SOLDERING FOOTPRINT\*



**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="https://www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative